

20V(D-S) N-Channel Enhancement Mode Power MOS FET

General Features

- $V_{DS} = 20V, I_D = 6A$
 $R_{DS(ON)} < 35m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=4.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

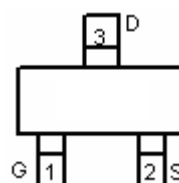


Lead Free

Application

- Uni-directional Load switch
- Bi-directional Load switch

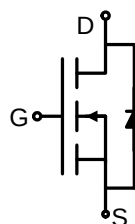
PIN Configuration



Marking and pin Assignment



SOT-23 top view



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
	MSN3420	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	6	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20	22	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =4.0 A	-	27	35	mΩ
		V _{GS} =4.5V, I _D =5.0A	-	20	28	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =6A	-	25	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =10V,V _{GS} =0V, F=1.0MHz	-	515	-	PF
Output Capacitance	C _{OSS}		-	90	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	72	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V, R _L =1.7Ω V _{GS} =10V,R _{GEN} =3Ω	-	3	-	nS
Turn-on Rise Time	t _r		-	7.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	20	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =10V,I _D =6A,V _{GS} =10V	-	12	-	nC
Gate-Source Charge	Q _{gs}		-	1	-	nC
Gate-Drain Charge	Q _{gd}		-	2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	6	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

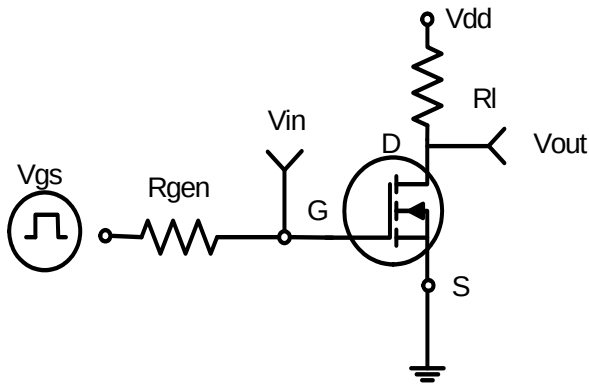


Figure 1: Switching Test Circuit

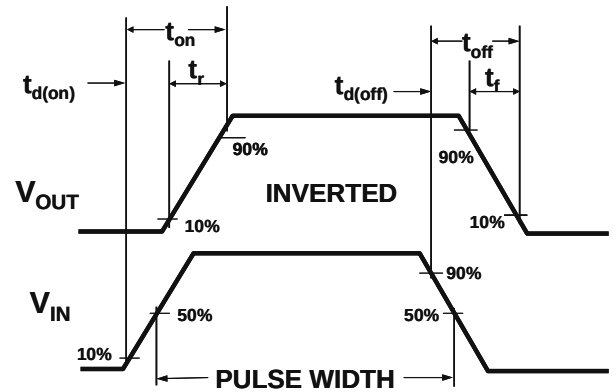


Figure 2: Switching Waveforms

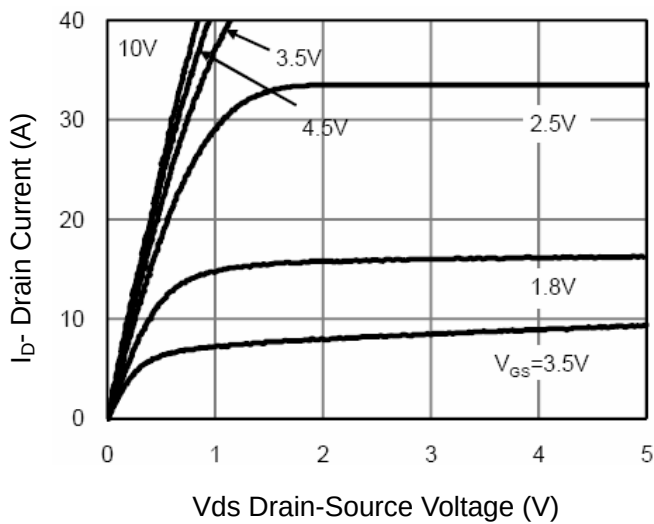


Figure 3: Output Characteristics

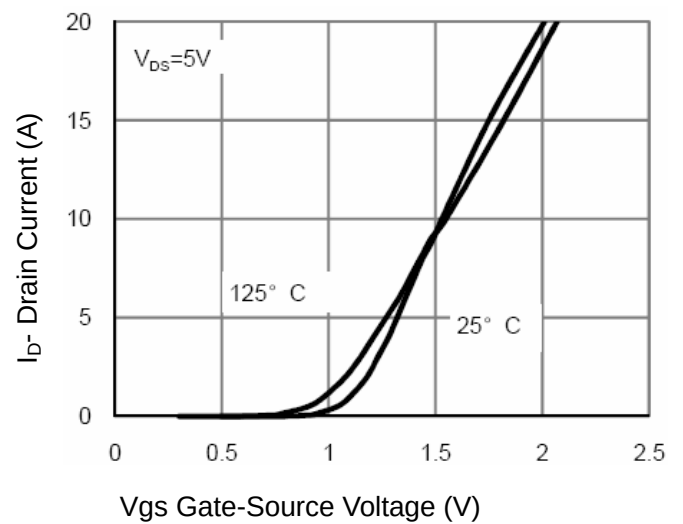


Figure 4: Transfer Characteristics

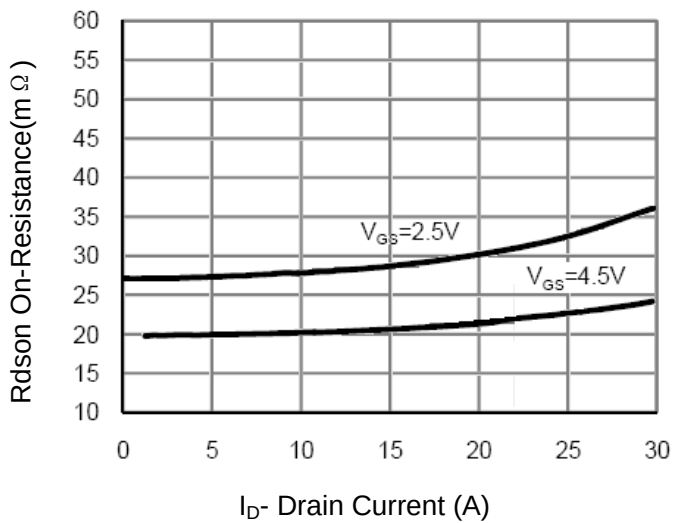


Figure 5: Drain-Source On-Resistance

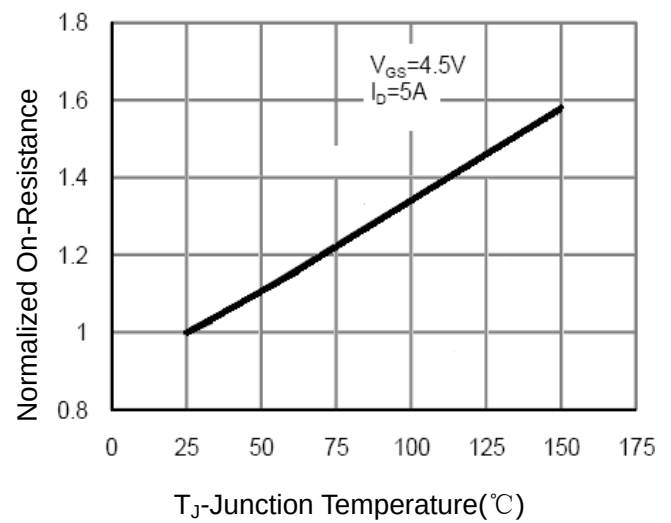
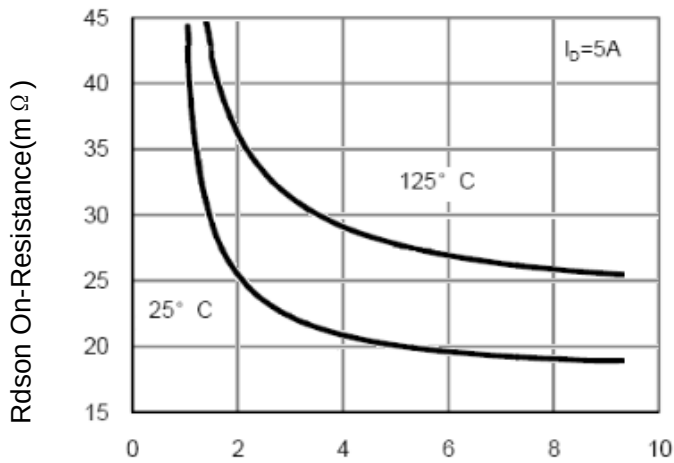
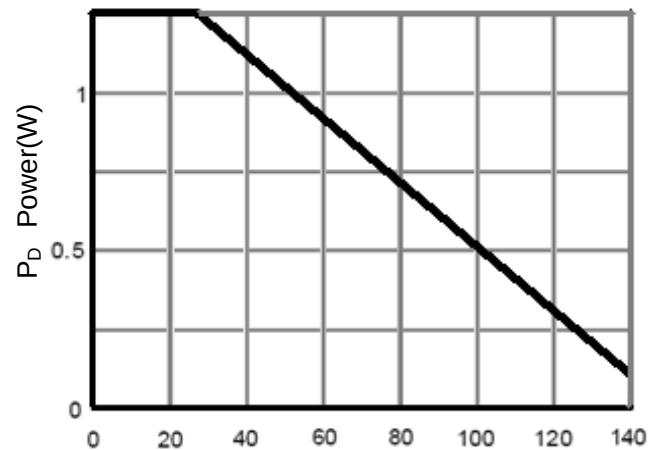


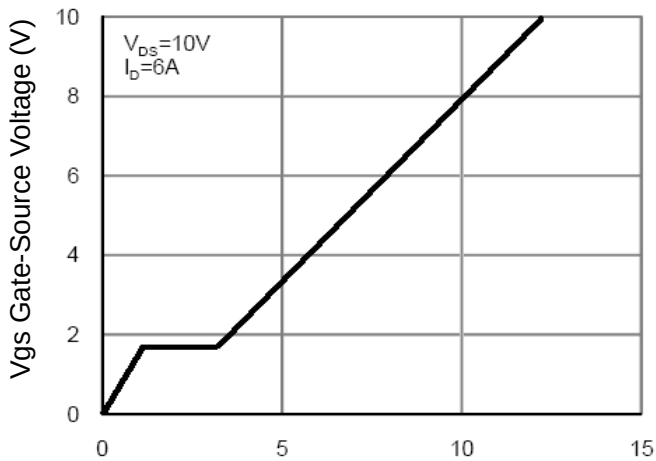
Figure 6: Drain-Source On-Resistance



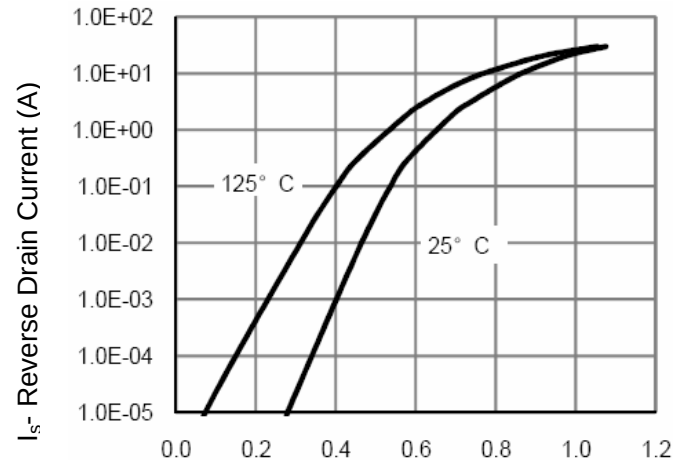
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



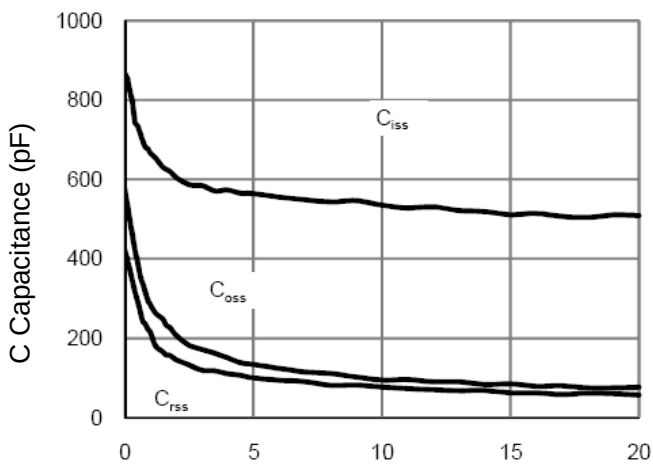
T_J-Junction Temperature(°C)
Figure 8 Power Dissipation



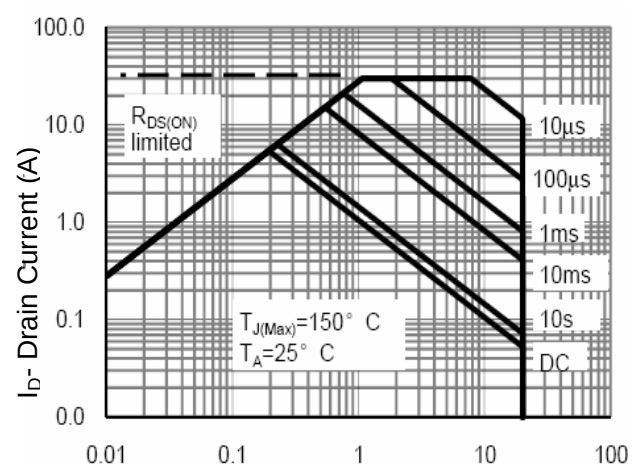
Qg Gate Charge (nC)
Figure 9 Gate Charge



Vds Drain-Source Voltage (V)
Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

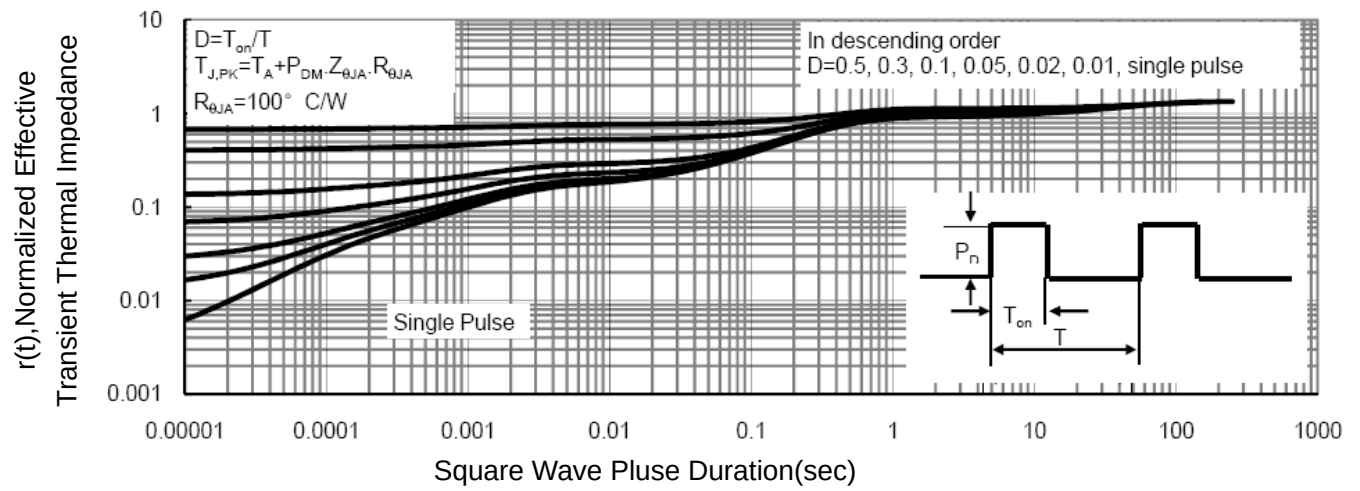
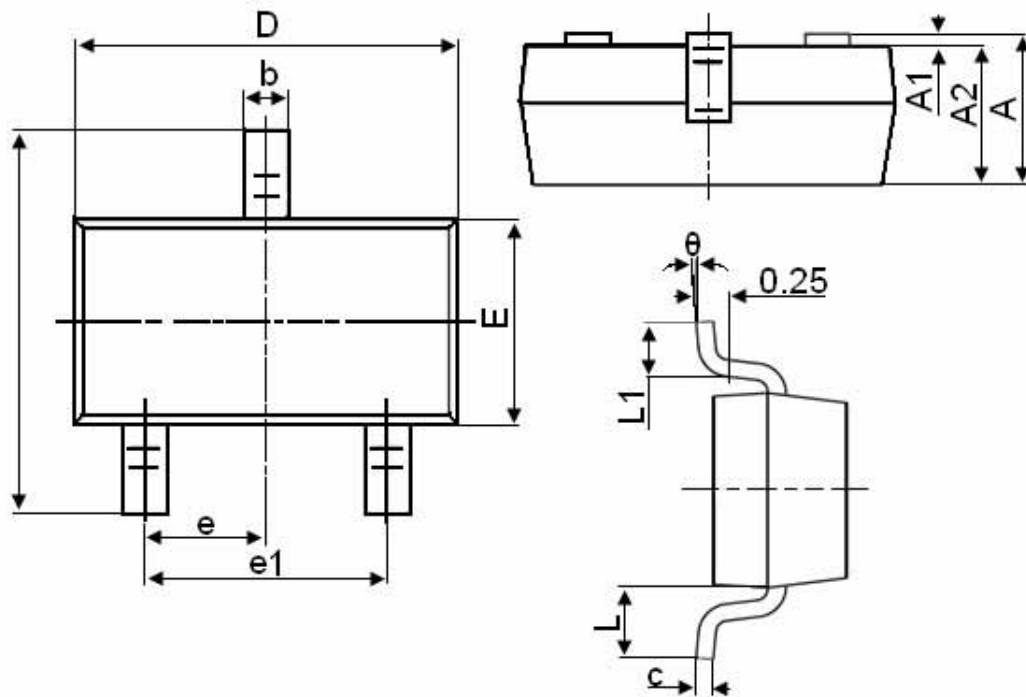


Figure 13 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.